

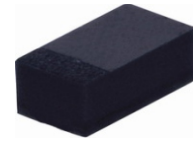
SMD Schottky Barrier Diode



SMD Diodes Specialist

CDBFR0245 (RoHS Device)

$I_o = 200 \text{ mA}$
 $V_R = 45 \text{ Volts}$

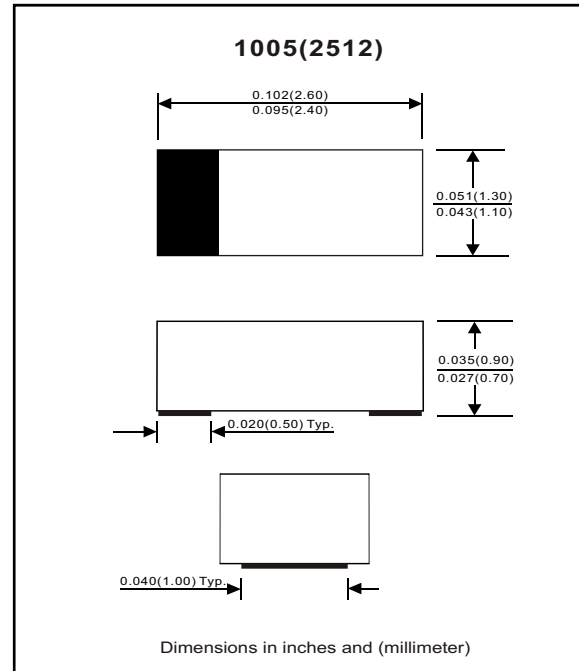


Features

- Designed for mounting on small surface.
- Extremely thin/leadless package.
- Low leakage current($I_R=0.1 \mu\text{A}$ typ. @ $V_R=10\text{V}$).
- Majority carrier conduction.

Mechanical data

- Case: 1005(2512) standard package, molded plastic.
- Terminals: Gold plated, solderable per MIL-STD-750, method 2026.
- Polarity: Indicated by cathode band.
- Mounting position: Any
- Weight: 0.006 gram(approx.).



Maximum Rating (at $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Repetitive peak reverse voltage		V_{RRM}			50	V
Reverse voltage		V_R			45	V
Average forward current		I_o			200	mA
Forward current, surge peak	8.3ms single half sine-wave superimposed on rate load(JEDEC method)	I_{FSM}		3000		mA
Power Dissipation		P_D			250	mW
Storage temperature		T_{STG}	-40		+125	$^\circ\text{C}$
Junction temperature		T_j	-40		+125	$^\circ\text{C}$

Electrical Characteristics (at $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 200 \text{ mA DC}$	V_F			0.55	V
Reverse current	$V_R = 10 \text{ V}$	I_R			1	μA
Capacitance between terminals	$f = 1 \text{ MHz}$, and 10VDC reverse voltage	C_T		9		pF

RATING AND CHARACTERISTIC CURVES (CDBFR0245)

Fig. 1 - Forward characteristics

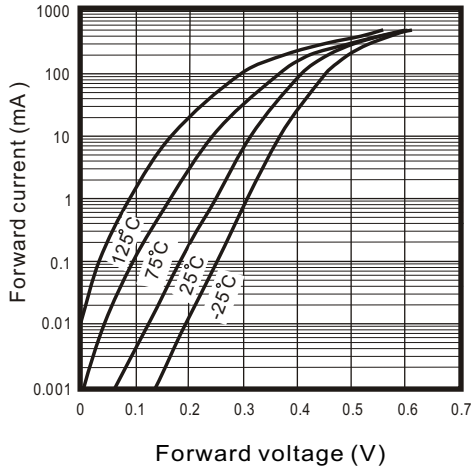


Fig. 2 - Reverse characteristics

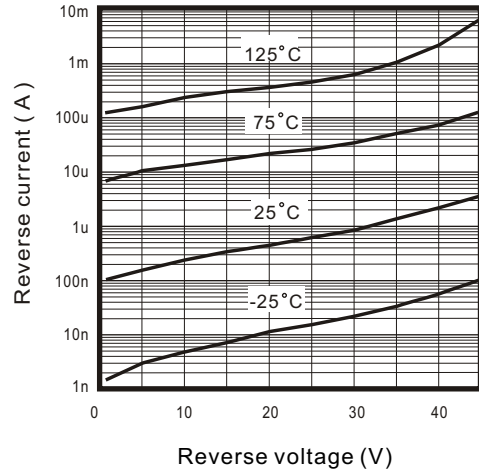


Fig. 3 - Capacitance between terminals characteristics

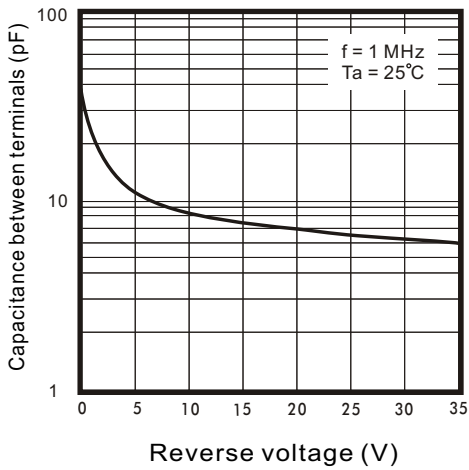


Fig. 4 - Current derating curve

